
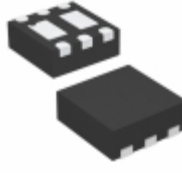
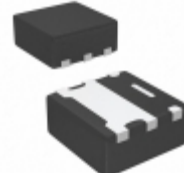
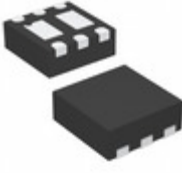
	<h2>SIB911DK-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIB911DK-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET 2P-CH 20V 2.6A SC75-6</p> <p>Datenblätter:  SIB911DK-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 163095 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIB911DK-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET 2P-CH 20V 2.6A SC75-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	163095 pcs Stock
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	3.1W
Verpackung / Gehäuse	PowerPAK® SC-75-6L Dual
Supplier Device-Gehäuse	PowerPAK® SC-75-6L Dual
Typ FET	2 P-Channel (Dual)
FET-Merkmal	Standard
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.6A
Rds On (Max) @ Id, Vgs	295 mOhm @ 1.5A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	4nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	115pF @ 10V
Verpackung	Tape & Reel (TR)







SIB911DK-T1-GE3 ist neu im Original, Suche SIB911DK-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIB911DK-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SIB911DK-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIB914DK-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 8V 1.5A PPAK SC75-6</p>	 <p>SIB900EDK-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 20V 1.5A SC- 75-6</p>	 <p>SIB800EDK-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 1.5A SC75- 6</p>	 <p>SIB900EDK-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 1.5A SC- 75-6</p>
 <p>SIB912DK-T1-GE3 Vishay / Siliconix MOSFET 2N-CH 20V 1.5A SC- 75-6</p>	 <p>SIB911DK-T1-E3 Vishay / Siliconix MOSFET 2P-CH 20V 2.6A SC75- 6</p>	 <p>SIB912DK-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2N-CH 20V 1.5A SC- 75-6</p>	 <p>SIB911DK-T1-GE3 Electro-Films (EFI) / Vishay MOSFET 2P-CH 20V 2.6A SC75- 6</p>

heiße Teile

Mehr

 1812AA221KATRE	 ADP3403ARU-REEL	 AZ431LBZTR-E1	 BUK7507-30B	 BZX84C39W-7-F
 C5750X7S2A685M200KB	 CC1206JKNPOZBN681	 CC1206KKX7R9BB225	 DMT3009LFVW-7	 ELM33414CA-S
 FGA20S120M	 GRM0336R1E8R7DD01D	 GRM31A5C3A820JW01D	 GRM31CR71E106KA12K	 HA11571BFEB
 IDT74LVC74APY	 IRFHM8363TR	 IXFN25N90	 IXTA110N055T7	 JMK325BJ226MM-T
 MDD56-16N1 B	 MUN5215T1G	 NFZ18SM121SN10D	 P6SMB33AT3G	 P6SMB9.1A
 PC928PYJ000F	 PCI6515AZHKG1	 PL62958E01	 SIB414DK-T1-GE3	 SIB414DK-T1-GE3
 SIB422EDK-T1-GE3	 SIB422EDK-T1-GE3	 SIB437EDKT-T1-GE3	 SIB437EDKT-T1-GE3	 SIB900EDK-T1-GE3
 SIB900EDK-T1-GE3	 SIB911DK-T1-GE3	 SIBA 10.NH000	 SKiiP38AC12T4V10	 SKIIP912GB120
 STD17NF25T4	 STK14CA8-NF45TR	 STP8NK80Z	 T2159N28TOF	 TA31275FNG
 TC7MBL3257AFK	 THD15-2411	 UFT12520C	 UP0126BJT3-12	 ZS1R52415

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